

Product Overview

MJE3055T: Bipolar Power Transistor, NPN, 10 A, 60 V, 75 Watt

For complete documentation, see the data sheet.

The Bipolar Power Transistor is designed for use in general-purpose amplifier and switching applications. The MJE2955T (PNP) and MJE3055T (NPN) are complementary devices.

Features

- DC Current Gain Specified to 10 Amperes
- High Current Gain - Bandwidth Product - $f_T = 2.0$ MHz (Min) @ $I_C f_T = 500$ mAdc
- Pb-Free Packages are Available

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Polarity	Type	$V_{CE(sat)}$ Max (V)	I_C Cont. (A)	V_{CEO} Min (V)	V_{CBO} (V)	V_{EBO} (V)	$V_{BE(sat)}$ (V)	$V_{BE(on)}$ (V)	h_{FE} Min	h_{FE} Max	f_T Min (MHz)	P_{TM} Max (W)	Package Type
MJE3055TG	0.3733	Pb-free non AEC-Q and PPAP	Active	NPN	General Purpose	8	10	60	70	5	1.1	1.8	20	100	2	125	TO-220-3

For more information please contact your local sales support at www.onsemi.com.

Created on: 12/3/2020